

**Amendments to the Specification:**

Please replace the last paragraph beginning on page 7 with the following-amended paragraph:

A suitable mechanism (not shown) would be associated with subatmospheric transfer chamber 12 for transferring the substrates into and out of the respective processors 14. Further, a vacuum exhaust line/foreline (not shown) would be associate associated with chamber 16 for providing/maintaining desired pressure within the chamber. Of course, the depicted apparatus 10 and processor chambers 14 are only exemplary. The concluding claims are in no way limited by the environment, but for the literal wording appearing in such claims, and without limiting or interpretative reference to the specification or drawings, and in accordance with the doctrine of equivalents.

Please replace the paragraph beginning at line 8 on page 8 with the following amended paragraph:

Referring to Figs. 1 and 2, ~~deposition processor 14~~ deposition processor 10 includes a semiconductor substrate deposition chamber 16 which will typically be at subatmospheric pressure during deposition processing. Such includes internal walls 18. In the depicted example, processor 14 is shown in the form of an ALD or other CVD processor chamber having an exemplary gas inlet 20, diagrammatically shown at the top, for injecting one or more precursor gasses to within chamber 16. A showerhead 22 is fed by inlet 20. A substrate holder 24 is received within deposition chamber 16, and is diagrammatically shown as having a semiconductor substrate 25 received thereatop. Substrate holder 24 is preferably mounted for elevational movement for raising and lowering substrate 25 relative to showerhead 22.